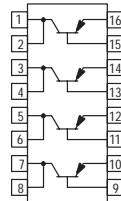
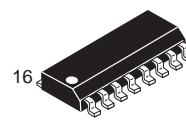


Quad General Purpose Transistors

PNP Silicon



MMPQ2907
MMPQ2907A



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CASE 751B-05, STYLE 4
SO-16

MAXIMUM RATINGS

Rating	Symbol	MMPQ2907	MMPQ2907A	Unit
Collector-Emitter Voltage	V_{CEO}	-40	-60	Vdc
Collector-Base Voltage	V_{CB}		-60	Vdc
Emitter-Base Voltage	V_{EB}		-5.0	Vdc
Collector Current — Continuous	I_C		-600	mAdc
		Each Transistor	Four Transistors Equal Power	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	0.52 4.2	1.0 8.0	Watts mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	0.8 6.4	2.4 19.2	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ⁽¹⁾ ($I_C = -10$ mA, $I_B = 0$)	MMPQ2907 MMPQ2907A	$V_{(BR)CEO}$	-40 -60	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = -10$ μ A, $I_E = 0$)		$V_{(BR)CBO}$	-60	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10$ μ A, $I_C = 0$)		$V_{(BR)EBO}$	-5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = -30$ Vdc, $I_E = 0$) ($V_{CB} = -50$ Vdc, $I_E = 0$)	MMPQ2907 MMPQ2907A	I_{CBO}	— —	— —	-50 -10	nAdc
Emitter Cutoff Current ($V_{EB} = -3.0$ Vdc, $I_C = 0$)		I_{EBO}	—	—	-50	nAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle = 2.0%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ⁽¹⁾ ($I_C = -100 \mu\text{Adc}$, $V_{CE} = -10 \text{ Vdc}$) ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$) ($I_C = -10 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$) ($I_C = -150 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$) ($I_C = -300 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$) ($I_C = -500 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$)	h_{FE}	75 100 75/100 100 30/50 50	— — — — — —	— — — 300 — —	—
Collector-Emitter Saturation Voltage ⁽¹⁾ ($I_C = -150 \text{ mAdc}$, $I_B = -15 \text{ mAdc}$) ($I_C = -300 \text{ mAdc}$, $I_B = -30 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	$V_{CE(\text{sat})}$	— — —	— — —	-0.4 -1.6 -1.6	Vdc
Base-Emitter Saturation Voltage ⁽¹⁾ ($I_C = -150 \text{ mAdc}$, $I_B = -15 \text{ mAdc}$) ($I_C = -300 \text{ mAdc}$, $I_B = -30 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	$V_{BE(\text{sat})}$	— — —	— — —	-1.3 -2.6 -2.6	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain — Bandwidth Product ⁽¹⁾ ($I_C = -50 \text{ mAdc}$, $V_{CE} = -20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	200	350	—	MHz
Output Capacitance ($V_{CB} = -10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	6.0	—	pF
Input Capacitance ($V_{EB} = -2.0 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ib}	—	20	—	pF

SWITCHING CHARACTERISTICS

Turn-On Time ($V_{CC} = -30 \text{ Vdc}$, $I_C = -150 \text{ mAdc}$, $I_{B1} = -15 \text{ mAdc}$)	t_{on}	—	30	—	ns
Turn-Off Time ($V_{CC} = -6.0 \text{ Vdc}$, $I_C = -150 \text{ mAdc}$, $I_{B1} = I_{B2} = -15 \text{ mAdc}$)	t_{off}	—	100	—	ns

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle = 2.0%.